





	<h2 style="color: #C00000;">FQD8P10TF_NB82052</h2>
	<p>Hersteller-Teilenummer: FQD8P10TF_NB82052</p> <p>Hersteller / Marke: AMI Semiconductor / ON Semiconductor</p> <p>Teil der Beschreibung: MOSFET P-CH 100V 6.6A DPAK</p> <p>Datenblätter:  FQD8P10TF_NB82052.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 32363 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	FQD8P10TF_NB82052
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET P-CH 100V 6.6A DPAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	32363 pcs Stock
detaillierte Beschreibung	P-Channel 100V 6.6A (Tc) 2.5W (Ta), 44W (Tc)
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-252-3, DPak (2 Leads + Tab), SC-63
Supplier Device-Gehäuse	D-Pak
Verlustleistung (max)	2.5W (Ta), 44W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	100V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	6.6A (Tc)
Rds On (Max) @ Id, Vgs	530 mOhm @ 3.3A, 10V
VGS (th) (Max) @ Id	4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	15nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	470pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±30V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)















































FQD8P10TF_NB82052 ist neu im Original, Suche FQD8P10TF_NB82052 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQD8P10TF_NB82052 AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage FQD8P10TF_NB82052: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>FQD8P10TM AMI Semiconductor / ON Semiconductor MOSFET P-CH 100V 6.6A DPAK</p>	 <p>FQD8P10TM_ Fairchild/ON Semiconductor FQD8P10TM_ FAIRCHILD</p>	 <p>FQD8P10TF AMI Semiconductor / ON Semiconductor MOSFET P-CH 100V 6.6A DPAK</p>	 <p>FQD8P10 FAIRCHI FQD8P10 FAIRCHI</p>
 <p>FQD8P10TM-F085 AMI Semiconductor / ON Semiconductor MOSFET P-CH 100V 6.6A DPAK-3</p>	 <p>FQD8P10TM Fairchild/ON Semiconductor MOSFET P-CH 100V 6.6A DPAK</p>	 <p>FQD8N60 FSC FQD8N60 FSC</p>	 <p>FQD8P10TF_NB82052 Fairchild/ON Semiconductor MOSFET P-CH 100V 6.6A DPAK</p>

heiße Teile

Mehr

 FQD6P25TM	 FQD6P25TM	 FQD7N10L	 FQD7N10LTF	 FQD7N10LTF
 FQD7N10LTM	 FQD7N10LTM	 FQD7N10TF	 FQD7N10TM	 FQD7N10TM
 FQD7N20L	 FQD7N20LTF	 FQD7N20LTF	 FQD7N20LTM	 FQD7N20LTM
 FQD7N20TF	 FQD7N20TF	 FQD7N20TM	 FQD7N20TM	 FQD7N30TM
 FQD7N30TM	 FQD7P06TF	 FQD7P06TF	 FQD7P06TM	 FQD7P06TM
 FQD7P06TM_F080	 FQD7P06TM_F080	 FQD7P06TM_NB82050	 FQD7P06TM_NB82050	 FQD7P10TF
 FQD7P20TF	 FQD7P20TF	 FQD7P20TM	 FQD7P20TM	 FQD7P20TM_F080
 FQD7P20TM_F080	 FQD8P10TF	 FQD8P10TF	 FQD8P10TF_NB82052	 FQD8P10TM
 FQD8P10TM	 FQD8P10TM_	 FQD8P10TM_F080	 FQD8P10TM_F080	 FQD8P10TM_F085
 FQD8P10TM_SB82052	 FQD8P10TM_SB82052	 FQD9N08L	 FQD9N25TM	 FQD9N25TM

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